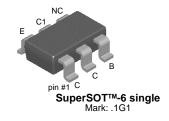


FMBSA06

NPN General Purpose Amplifier

- This device is designed for general purpose amplifier applications at collector currents to 300 mA.
- · Sourced from Process 12.



Absolute Maximum Ratings* T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	80	V
V_{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characte	eristics				•
V _{(BR)CEO}	Collector-Emitter Sustaining Voltage *	$I_C = 1.0 \text{mA}, I_B = 0$	80		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	4.0		V
CEO	Collector Cut-off Current	$V_{CE} = 60V, I_{B} = 0$		0.1	μΑ
СВО	Collector Cut-off Current	$V_{CB} = 80V, I_{E} = 0$		0.1	μΑ
On Characte	eristics				•
h _{FE}	DC Current Gain	I _C = 10mA, V _{CE} = 1.0V	100		
		$I_C = 100 \text{mA}, V_{CE} = 1.0 \text{V}$	100		
√ _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 100 \text{mA}, I_B = 10 \text{mA}$		0.25	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 10 \text{mA}, V_{CE} = 1.0 \text{V}$		1.2	V
	I Characteristics				
f _T	Current Gain Bandwidth Product	$I_C = 10$ mA, $V_{CE} = 2.0$ V, $f = 100$ MHz	100		MHz
Pulse Test: Pulse	Width ≤ 300μs, Duty Cycle ≤ 2.0%	•			

Thermal Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P_{D}	Total Device Dissipation *	700	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, total	180	°C/W

^{*} Device mounted on a 1 in 2 pad of 2 oz copper.

Typical Characteristics

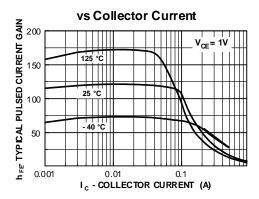


Figure 1. Typical Pulsed Current Gain vs Collector Current

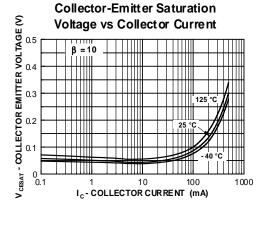


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

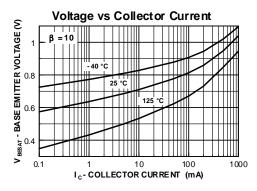


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

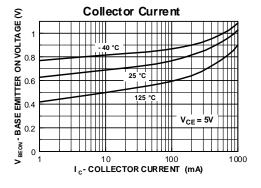


Figure 4. Base-Emitter On Voltage vs Collector Current

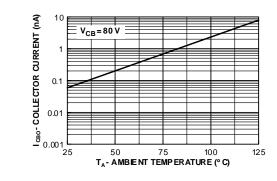


Figure 5. Collector Cutoff Current vs Ambient Temperature

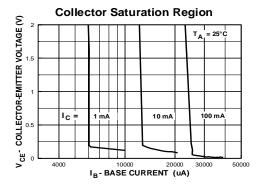


Figure 6. Collector Saturation Region

Rev. A1, November 2004

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Typical Characteristics (Continued)

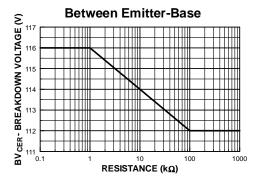


Figure 7. Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

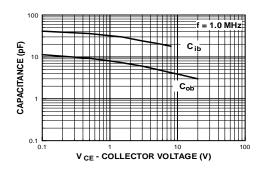


Figure 8. Input and Output Capacitance vs Reverse Voltage

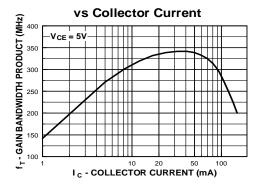
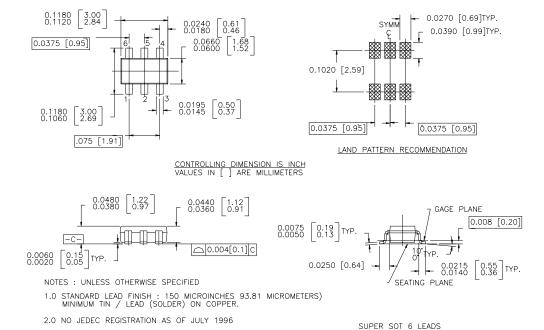


Figure 9. Gain Bandwidth Product vs Collector Current

Package Dimensions

SuperSOT™-6



Dimensions in Millimeters

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EnSigna™	i-Lo™	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect™	OCXPro™	RapidConnect™	UHC™
FACT Quiet Series™		OPTOLOGIC [®]	μSerDes™	UltraFET [®]
Across the board. Around the world.™		OPTOPLANAR™	SILENT SWITCHER®	VCX TM
The Power Franchise®		PACMAN™	SMART START™	
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